

TOSHIBA TRANSISTOR SILICON EPITAXIAL PLANAR TYPE

HN1V01H

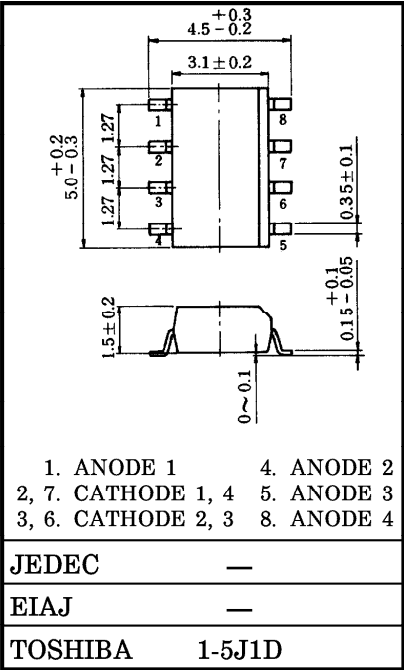
AM RADIO BAND TUNING APPLICATIONS.

Unit in mm

- High Capacitance Ratio : C1V / C8V = 19.5 (Typ.)
- High Q : Q = 200 (Min.)
- Including Four Devices in FM8 Package (Flat Pack Mini 8Pin)
- Low Voltage Operation : VR = 1~8V

MAXIMUM RATINGS (Ta = 25°C) (D1, D2, D3, D4)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	VR	16	V
Junction Temperature	Tj	125	°C
Storage Temperature Range	Tstg	-55~125	°C



ELECTRICAL CHARACTERISTICS (Ta = 25°C) (D1, D2, D3, D4)

Weight : 0.05g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	VR	IR = 10μA	16	—	—	V
Reverse Current	IR	VR = 16V	—	—	20	nA
Capacitance	C1V	VR = 1V, f = 1MHz	435	—	540	pF
Capacitance	C3V	VR = 3V, f = 1MHz	140	—	250	pF
Capacitance	C5V	VR = 5V, f = 1MHz	50.0	—	90.0	pF
Capacitance	C8V	VR = 8V, f = 1MHz	19.9	—	26.7	pF
Capacitance	C1V / C8V	—	16.2	19.5	—	—
Figure of Merit	Q	VR = 1V, f = 1MHz	200	—	—	—

Note 1 : Four Devices in one Package are matched for capacitance to 2.5%.

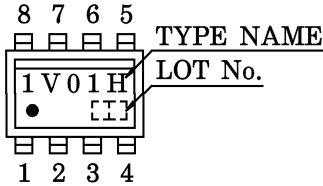
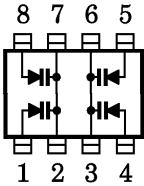
PIN ASSIGNMENT (TOP VIEW)

MARKING

$$\frac{C(\text{Max.}) - C(\text{Min.})}{C(\text{Min.})} \leq 0.025 \quad (V_R = 1 \sim 8V)$$

Note 2 : C8V is divided into two classifications as follows.

Classification	C8V (pF)
A	19.9~23.7
B	22.4~26.7



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